

<p style="text-align: center;">INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p> <p style="text-align: center;">JAN 07 2004</p> <p style="text-align: center;">EXAMINER <i>[Signature]</i> INITIALS <i>[Initials]</i></p>		Docket Number (Optional) FIS920030300	Application Number 10/707,009
		Applicant(s) Furukawa et al.	
		Filing Date 11-13-03	Group Art Unit
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
<p>Homma et al., "A Selective SiO₂ Film-Formation Technology Using Liquid-Phase Deposition for Fully Planarized Multilevel Interconnections", J. Electrochem. Soc., Vol. 140, No. 8, 1993, pp. 2410-2414.</p>			
<p>Ching-Fa Yeh, et al., "Comprehensive Investigation on Fluorosilicate Glass Prepared by Temperature-Difference-Based Liquid-Phase Deposition", J. Electrochem. Soc., Vol. 147, No. 1, 2000, pp. 330-334.</p>			
<p>Nagayama et al., "A New Process for Silica Coating", J. Electrochem. Soc., Vol. 135, No. 8, 1988, pp. 2013-2016.</p>			
<p>Homma et al., "Optical Properties of Fluorinated Silicon Oxide and Organic Spin-on-Glass Films for Thin-Film Optical Waveguides", J. Electrochem. Soc., Vol. 147, No. 3, 2000, pp. 1141-1144.</p>			
<p>Ching-Fa Yeh et al., "Novel Barrier Dielectric Liner Prepared by Liquid-Phase Deposition and NH₃ Plasma Annealing", Journal of Appl. Phys. Vol. 39, 2000, pp. 6672-6675.</p>			
EXAMINER <i>[Signature]</i> INITIALS <i>[Initials]</i>		DATE CONSIDERED <i>6-29-05</i>	

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

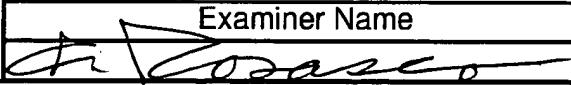
ELECTRONIC INFORMATION DISCLOSURE STATEMENT

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Title of Invention	ALTERNATING PHASE MASK BUILT BY ADDITIVE FILM DEPOSITION						
<p>Application Number :</p> <p>Confirmation Number:</p> <p>First Named Applicant: Toshiharu Furukawa</p> <p>Attorney Docket Number: FIS920030300</p> <p>Art Unit:</p> <p>Examiner:</p> <p>Search string: (4468420 or 4693916 or 4770901 or 4882183 or 5073408 or 5114760 or 5132140 or 5614270 or 5648128 or 5661051 or 6251753 or 6294832).pn</p>							
US Patent Documents							
Note: Applicant is not required to submit a paper copy of cited US Patent Documents							
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
1	4468420	1984-08-28	Kawahara et al.				
2	4693916	1987-09-15	Nagayama et al.				
3	4770901	1988-09-13	Katoh et al.				
4	4882183	1989-11-21	Ino et al.				
5	5073408	1991-12-17	Goda et al.				
6	5114760	1992-05-19	Takemura et al.				
7	5132140	1992-07-21	Goda et al.				
8	5614270	1997-03-25	Yeh et al.				
9	5648128	1997-07-15	Yeh et al.				
10	5661051	1997-08-26	Yeh et al.				
11	6251753	2001-06-26	Yeh et al.				
12	6294832	2001-09-25	Yeh et al.				

Signature

Examiner Name	Date
	6-29-05